## **SPTECH Silicon NPN Power Transistors**

2N6678

#### **DESCRIPTION**

- · High Voltage Capability
- · Fast Switching Speed
- Low Saturation Voltage

#### **APPLICATIONS**

Designed for high voltage switching applications such as:

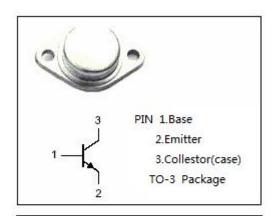
- Off-line power supplies
- Converter circuits
- PWM regulators

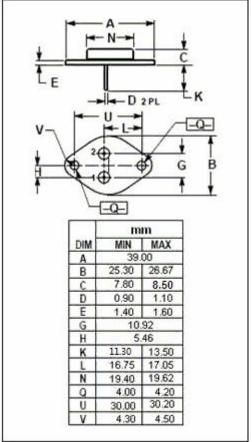
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CEV</sub>	Collector-Emitter Voltage	650	V
V <sub>CEX</sub>	Collector-Emitter Voltage	450	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	٧
V <sub>EBO</sub>	Emitter-Base Voltage 8.0		٧
Ic	Collector Current-Continuous 19		Α
I <sub>CM</sub>	Collector Current-Peak 20		Α
I <sub>B</sub>	Base Current-Continuous	5.0	Α
Pc	Collector Power Dissipation@T <sub>C</sub> =25℃	175	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.0	°C/W





SPTECH website: www.superic-tech.com

# **SPTECH Silicon NPN Power Transistors**

2N6678

## **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	Ic=50mA; I <sub>B</sub> =0	400		V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3.0A		1.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3.0A		1.5	V			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 8.0V; I <sub>C</sub> =0		2.0	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 3V	8.0					
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = 1.0A; V <sub>CE</sub> = 10V; f <sub>test</sub> =5.0MHz	3.0		MHz			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =0.1MHz		500	pF			
Switching times								
t <sub>d</sub>	Delay Time	$I_{C}$ = 15A , $V_{CC}$ = 200V, $I_{B1}$ = - $I_{B2}$ = 3A, $t_p$ =20 μ s, Duty Cycle ≤2.0% $V_{BB}$ =6V, $R_L$ =13.5 $Ω$		0.2	μs			
t <sub>r</sub>	Rise Time			0.6	μs			
t <sub>s</sub>	Storage Time			2.5	μs			
t <sub>f</sub>	Fall Time			0.6	μs			

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SPTECH manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B